

L Number	Hits	Search Text	DB	Time stamp
-	5	((("5838041") or ("5969383")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 12:01
-	1604	(nonvolat\$4 adj2 memory) with (first adj2 second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 12:05
-	16	((nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)) and (gate adj electrode)) and (first near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 12:08
-	6	(((((nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)) and (gate adj electrode)) and (first near3 region)) and (second near3 gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 12:10
-	36	(nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 12:12
-	26	((nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:46
-	36942	nonvolat\$4 adj2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:20
-	569	(nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) same (second near2 gate near2 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:55
-	419	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) same (second near2 gate near2 electrode))) and ((first or second) near4 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:54
-	52	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) same (second near2 gate near2 electrode))) and ((first or second) near4 region near4 (p adj type))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:34
-	2	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) same (second near2 gate near2 electrode))) and ((first or second) near4 region near4 (first adj type))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:14
-	371	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) same (second near2 gate near2 electrode))) and ((first or second) near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:56

-	515	(nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:55
-	515	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:55
-	344	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first or second) near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:08
-	344	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first or second) near2 region)) and ((first or second) field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:09
-	2	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first or second) near2 region)) and ((first or second) field adj effect)) and ((first or second) near4 region near4 ((first or second) adj type))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:18
-	0	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and (((first or second) adj region) near4 ((first or second) adj type))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:19
-	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:20
-	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:20
-	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:49
-	0	257/257,316,319,321,324,326,315,311,322,326.ccls. and 438/258,592,182,257-267,736,738,592 and ((first or second) adj gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:53
-	1	(257/257,316,319,321,324,326,315,311,322,326.ccls. and 438/258,592,182,257-267,736,738,592.ccls. and ((first or second) adj gate adj electrode)) and 365/185.01,185.18.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:56
-	46	257/257,316,319,321,324,326,315,311,322,326.ccls. and 438/258,592,182,257-267,736,738,592.ccls. and ((first or second) adj gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:26
-	8	(257/257,316,319,321,324,326,315,311,322,326.ccls. and 438/258,592,182,257-267,736,738,592.ccls. and ((first or second) adj gate adj electrode)) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:28